

2SK1606

Silicon N-Channel Power F-MOS FET

■ Features

- High avalanche energy capacity
- V_{GS} : 30V guaranteed
- Low $R_{DS(on)}$, high-speed switching characteristic

■ Applications

- High-speed switching (switching power supply)
- For high-frequency power amplification

■ Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit	
Drain to Source breakdown voltage	V_{DSS}	450	V	
Gate to Source voltage	V_{GSS}	± 30	V	
Drain current	DC	I_D	± 8	A
	Pulse	I_{DP}	± 16	A
Avalanche energy capacity	EAS*	130	mJ	
Allowable power dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_a = 25^\circ\text{C}$		2	
Channel temperature	T_{ch}	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

* Single pulse

■ Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 360\text{V}$, $V_{GS} = 0$			0.1	mA	
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0$			± 1	μA	
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	450			V	
Avalanche energy capacity	EAS*	$L = 4.1\text{mH}$, $I_D = 8\text{A}$, $V_{DD} = 50\text{V}$	130			mJ	
Gate threshold voltage	V_{th}	$V_{DS} = 25\text{V}$, $I_D = 1\text{mA}$	1		5	V	
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 4\text{A}$		0.56	0.75	Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25\text{V}$, $I_D = 4\text{A}$	3	5		S	
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 20\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		1300		pF	
Output capacitance (Common Source)	C_{oss}				160		pF
Reverse transfer capacitance (Common Source)	C_{rss}				70		pF
Turn-on time	t_{on}	$V_{GS} = 10\text{V}$, $I_D = 4\text{A}$ $V_{DD} = 150\text{V}$, $R_L = 37.5\Omega$		70		ns	
Fall time	t_f				50		ns
Turn-off time (delay time)	$t_{d(off)}$				150		ns

* Avalanche energy capacity test circuit



